ABSTRACT OF THE DISCLOSURE

The present provides a method of producing a semiconductor device, which method comprises cleaning with a rinse in the form of water containing a peroxide after removal of a photoresist with a removing agent in the course of removal of the photoresist applied to a conductive metal film formed on a semiconductor wafer, and a rinse for cleaning semiconductor devices.

According to the present invention, in a method of producing a semiconductor device wherein, for example, a photoresist film applied on an aluminum conductive film formed on a semiconductor wafer, a photoresist layer after dry-etching, or any photoresist residue remaining after dry-etching followed by ashing is removed with a remover, there can be provided a method of producing a highly accurate circuital wiring safely without corroding the conductive metal film at all.

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